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# M66515FP

# Laser Diode Driver/Controller

REJ03F0084-0100Z Rev.1.0 Sep.22.2003

### **Description**

The M66515 is a laser diode driver/controller that performs drive and controls the laser power control of a type of semiconductor laser diode the anode of which is connected, with the cathode of a photodiode for monitoring, to a stem in which the semiconductor laser diode anode and monitoring photo diode cathode are connected to the stem.

This IC has a sink-type laser driving current output pin, and can drive a laser diode with a bias current of up to a maximum 30 mA and with switched currents of up to 120 mA, switched at rates of up to 40 Mbps.

The IC incorporates a sample hold circuit, so that a self-APC (Automatic Power Control) system, which does not require external laser power control, can be realized.

#### **Features**

- Internal sample-and-hold circuit for self-APC configuration
- High-speed switching (40 Mbps)
- High driving currents (150 mA max)
- Settable bias current (30 mA max)
- Single 5 V power supply

## **Applications**

• Equipment employing semiconductor laser diodes

#### **Function Overview**

The M66515 is a laser diode driver/controller which drives and controls the laser power of a semiconductor laser diode (LD) the anode of which is connected, with the cathode of a photodiode (PD) for monitoring, to a stem (among Mitsubishi lasers, N type models).

LD driving and laser power control are executed by connecting an external capacitance to the  $C_H$  pin and applying a reference voltage to the  $V_r$  pin.

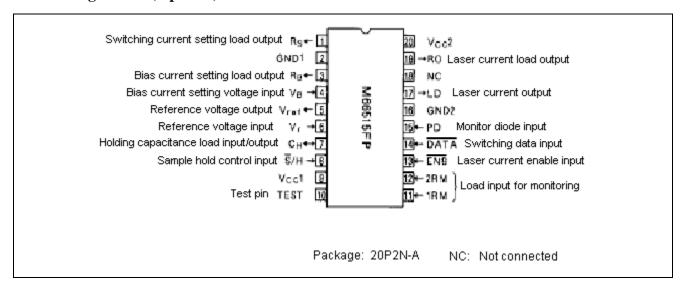
The PD current occurring when a LD emits light flows through a resistance connected across 1RM and 2RM, resulting in a potential difference  $(V_M)$ . This  $V_M$  is compared with the voltage applied to the  $V_r$  pin, and when  $V_M < V_r$ , a constant current source from the  $C_H$  pin flows to charge the external capacitor. When  $V_M > V_r$ , a constant current sink from the  $C_H$  pin causes the charge on the external capacitor to be discharged.

This operation is performed when the  $\overline{S}/H$  input is "L" (sample); when the  $\overline{S}/H$  input is in the "H" state, the  $C_H$  pin is in the high-impedance state (hold), regardless of  $V_M$ ,  $V_r$  and the  $\overline{DATA}$  input state.

The LD driving current consists of a switched current  $I_{SW}$ , which is controlled by the  $\overline{DATA}$  input, and  $I_B$ , a LD bias current which is independent of the  $\overline{DATA}$  input state.



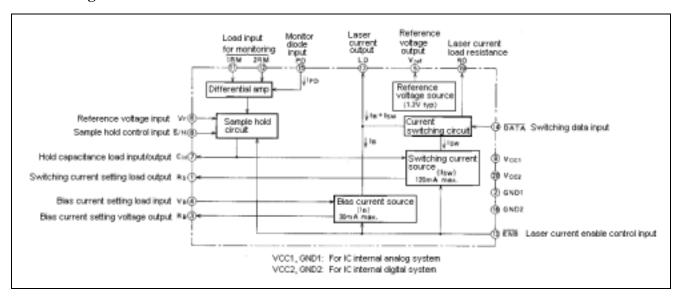
## **Pin Configuration (top view)**



# **Description of Pin**

Pin name	Name	Function
LD	Laser current output	Connected to the semiconductor LD cathode
PD	Monitor diode input	Connected to the monitor PD anode
R <sub>S</sub>	Switching current setting load output	Connects the load resistance to set the current for switching ( $I_{\text{SW}}$ ) to GND
R <sub>B</sub>	Bias current setting load output	Connects the load resistance to set the bias current ( $I_B$ ) to GND. If $I_B$ is not used, this pin should be left open.
V <sub>B</sub>	Bias current setting voltage input	The bias current value ( $I_B$ ) can be set by applying a voltage to this pin. If $I_B$ is not used, this pin should be left open.
DATA	Switching data input	At "L", the current I <sub>SW</sub> +I <sub>B</sub> flows to the LD; at "H", the current to the LD is I <sub>B</sub>
1RM, 2RM	Load input for monitoring	Connect a load resistance to convert the monitor PD current to a voltage across 1RM and 2RM
ENB	Laser current enable input	When "H", all current source circuits are turned off
RO	Laser current load output	Connect a laser current load resistance between this pin and V <sub>CC</sub>
S/H	Sample hold control input	When "L", sample (APC) operation is performed; when "H", hold (switching) is performed
СН	Hold capacitor load input/output	Connect a hold capacitor between this pin and GND. This pin is connected within the M66515 to the sample hold circuit output and $I_{\text{SW}}$ current source input.
Vref	Reference voltage output	Output pin for the M66515 internal reference voltage (1.2 V typ)
Vr	Reference voltage input	A reference voltage is applied to cause operation of the comparator within the sample hold circuit. When using the reference voltage within the M66515, this pin should be connected to the $V_{\text{ref}}$ pin.
TEST	Test pin	Pin used for testing at time of shipment of the M66515; should be left open
V <sub>CC</sub> 1	Power supply pin 1	Power supply for the internal analog system; connect to a positive power supply (+5 V)
V <sub>CC</sub> 2	Power supply pin 2	Power supply for the internal digital system; connect to a positive power supply (+5 V)
GND1	GND pin 1	GND for internal analog system
GND2	GND pin 2	GND for internal digital system

## **Block Diagram**



## **Explanation of operation**

#### 1. Laser driving current values

The values of the laser driving currents  $I_{SW}$  and  $I_B$  can be approximated as follows, if  $V_C$  is the voltage of the hold capacitor connected to the  $C_H$  pin.

(1) I<sub>SW</sub> (switched current)

$$l_{SW}$$
 [mA]= $12 \times \frac{V_{C}[V]}{R_{S}[k\Omega]}$ 

Here  $0 \le V_C \le V_{CC}$ -1.8 V,  $I_{SW}$  (max) =120 mA, and  $R_S$  is the value of the resistance connected between the  $R_S$  pin and GND

(2) I<sub>B</sub> (bias current)

$$l_B [mA] = 10 \times \frac{V_B[V]}{R_B[k\Omega]}$$

Here  $0 \le V_B \le V_{CC}$ -2.7 V,  $I_B$  (max) =30 mA, and  $R_B$  is the value of the resistance connected between the  $R_B$  pin and GND

### 2. Switching operation

When  $\overline{DATA}$ ="L", the LD driving current is  $I_{SW}$ + $I_B$ ; when  $\overline{DATA}$ ="H", the LD driving current is  $I_B$ .

#### 3. ENB input

Whereas the laser driving current is controlled by  $\overline{DATA}$  input by controlling the driving current applied to the laser with the current source in the M66515 turned on, control by  $\overline{ENB}$  turns the current source operation on and off.

When ENB="L" the current source is turned on, and when ENB="H" the current source is turned off.

When  $\overline{ENB}$ ="H", the  $C_H$  pin is forced to "L" level, and the charge on the capacitor connected to the  $C_H$  pin is forcibly discharged.

#### 4. Internal reset operation

The M66515 incorporates a reset circuit to prevent the flow of excessive current to the laser when power is turned on; when  $V_{CC}$ <3.5 V (typ), the internal current source is turned off and the  $C_H$  pin is forced to "L" level.

#### 5. RO pin

The RO pin is connected to the laser driving current load resistance; current essentially equal to  $I_{SW}$  flows from this pin. The load resistance is connected between this pin and  $V_{CC}$ ; by this means the Power dissipation within the IC is reduced.

However, the circuit operation requires that the voltage at this pin be 2.5 V or above. Hence if the maximum value of  $I_{SW}$  is  $I_{SW}(max)$ , then the maximum value RO(max) of the load resistance RO is as follows.

RO(max.) [Q] = 
$$\frac{V_{CC}(\min) - 2.5[V]}{I_{SW}(\max_{i})[A]}$$

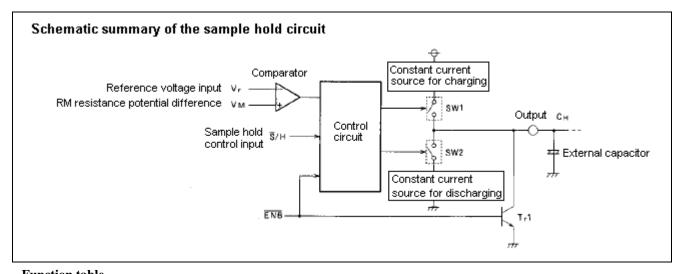
For example, if  $V_{CC}(min)=4.75$  V and  $I_{SW}(max)=120$  mA, then RO(max)=18.8  $\Omega$ . In other words, when setting the resistance  $R_S$  such that the maximum value of  $I_{SW}$  is 120 mA, RO should be 18.8  $\Omega$  or lower.

#### 6. Sample-and-hold circuit

#### (1) Summary of circuit operation

The following is a summary of operation of the sample hold circuit within the M66515.

A PD current arising upon LD light emission flows through the resistance connected between 1RM and 2RM, giving rise to a potential difference  $(V_M)$ . This  $V_M$  is compared with the voltage applied to the pin  $V_r$ , and if  $V_M < V_r$ , pin  $C_H$  is a constant current source which charges the external capacitor. If  $V_M > V_r$ , pin  $C_H$  is a constant current sink which discharges the external capacitor. This operation is performed when the  $\overline{S}$ /H input is "L" (sample); when the  $\overline{S}$ /H input is "H", the  $C_H$  pin is kept in the high-impedance state (hold), regardless of  $V_M$ ,  $V_r$ , and the  $\overline{DATA}$  input state.



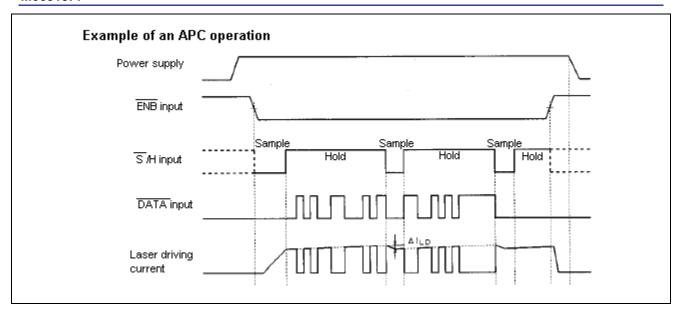
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Input	Input		Switche	Switched state		Output
ENB S/H Vm, Vr		SW1	SW1 SW2			
Н	Χ	Х	OFF	OFF	ON	Fixed at "L"
L	Н	Χ	OFF	OFF	OFF	High-impedance state (hold)
L	L	$V_M < Vr$	ON	OFF	OFF	Constant current source (sample)
		$V_M > Vr$	OFF	ON	OFF	Constant current sink (sample)

X: arbitrary

#### (2) APC operation timing chart

An example of an APC operation timing chart for a given sample hold control signal is shown below.

In this example, a case is shown in which it is assumed that the direction of the leakage current of the  $C_H$  pin in the hold state is the direction flowing out from the M66515 (the negative direction).



## 7. $V_{CC}$ and GND pins

The  $V_{CC}1$  and  $V_{CC}2$  pins and the GND1 and GND2 pins are related to the power supply. The internal circuitry connected to these pins is as follows.

V<sub>CC</sub>1, GND1: Connected to analog circuitry

V<sub>CC</sub>2, GND2: Connected to digital circuitry

The following should be taken into account in designing the actual wiring.

- (1) Wiring widths should be as broad as possible, and drawn-out lengths of wiring should be avoided.
- (2) The electrolytic capacitor for voltage stability should be positioned close to  $V_{CC}1$  and GND1.
- (3) The bypass capacitor should be positioned close to  $V_{CC}2$  and GND2.

#### **Important Information Regarding Peripheral Element Wiring**

Peripheral elements necessary for M66515 operation should be positioned as close to the M66515 as possible.

#### Method of Calculating Power dissipation

The M66515 Power dissipation P is essentially given by the following formula.

$$\mathsf{P} = \mathsf{I}_{\mathsf{CC}} \times \mathsf{V}_{\mathsf{CC}} + \mathsf{I}_{(\mathsf{RO})} \times \mathsf{I}_{(\mathsf{RO})} + \mathsf{I}_{(\mathsf{LD})} \times \mathsf{V}_{(\mathsf{LD})}$$

Here  $V_{(RO)}$  is the RO pin voltage,  $V_{(LD)}$  is the LD pin voltage,  $I_{(RO)}$  is the RO pin load current, and  $I_{(LD)}$  is the LD pin load current.

For example, when  $V_{CC} = 5.25 \text{ V}$ ,  $V_{(RO)} = V_{(LD)} = 2.5 \text{ V}$ , and  $I_{(RO)} = I_{(LD)} = 150 \text{ mA}$ , the Power dissipation when the laser is turned on and off is as follows.

(1) When the laser is on ( $\overline{DATA}$  = "L",  $I_{CC}$  = 75 mA):

$$P_{ON} = 75 \times 5.25 + 0 + 150 \times 2.5 = 768.8$$
 (mW)

(2) When the laser is off ( $\overline{DATA}$  = "H",  $I_{CC}$  = 74 mA):

$$P_{OFF} = 74 \times 5.25 + 0 + 150 \times 2.5 = 763.5 \text{ (mW)}$$

# **Absolute Maximum Ratings**

(Unless otherwise noted, Ta = -20 to  $70^{\circ}$ C)

Symbol	Parameter		Conditions	Value	Unit
V <sub>CC</sub>	Power supply voltage			-0.5 to +7.0	V
Vı	Input voltage	CH, Vr		−0.3 to V <sub>CC</sub>	V
		DATA, ENB, S/H		-0.3 to +7.0	V
Vo	Output voltage	RO		-0.5 to +7.0	V
I <sub>SW</sub>	Switching current			150	mA
I <sub>B</sub>	Bias current			45	mA
Pd	Power dissipation		Mounted on board, with	1200	mW
			Ta=25°C (see note)		
Tstg	Storage temperature			-60 to +150	°C

Note: When  $Ta \ge 25$ °C, derating at 9.6 mW/°C should be performed.

# **Recommended Operating Conditions**

(Unless otherwise noted, Ta = -20 to  $70^{\circ}$ C)

Symbol	Parameter	Limits	Unit		
		Min	Тур	Max	
V <sub>CC</sub>	Power supply voltage	4.75	5.0	5.25	V
I <sub>SW</sub>	Switching current			120	mA
I <sub>B</sub>	Bias current			30	mA
Topr	Operating ambient temperature	-20	_	70	°C

## **Electrical Characteristics**

(Unless otherwise noted,  $V_{CC} = 5 \text{ V} \pm 5\%$ ,  $Ta = -20 \text{ to } 70^{\circ}\text{C}$ )

Sym-	Parameter			Measurement conditions L			Limits			Mea-
bol							Тур	Max	_	sure- ment cir- cuit
V <sub>IH</sub>	"H" input voltage	DATA, E	NB, S/H			2.0			V	
$V_{IL}$	"L" input voltage	DATA, E	NB, S/H					0.8	V	
Vr	Reference voltage input	Vr				0.4		2.0	V	
Vref	Reference	Vref		$I_0 = -10  \mu A$			1.2		V	1
	voltage output	Tempera	ature	Ta = −20 to 25°C			-0.9		mV/°C	•
		coefficie	nt	Ta = 25 to 70°C			-0.9		_	
$V_{LD}$	Operating voltage range	LD				2.5		V <sub>CC</sub>	V	
Vı	Effective voltage upper limit	Сн				V <sub>CC</sub> - 1.8	V <sub>CC</sub> - 1.4		V	
V <sub>OH</sub>	"H" output voltage	Сн		$\overline{\text{ENB}} = 0.8 \text{ V}, I_{\text{OH}} = -2 \text{ mA}$		4.0			V	1
V <sub>OL</sub>	"L" output voltage	Сн		$\overline{\text{ENB}} = 0.8 \text{ V}, I_{\text{OL}} = 2 \text{ mA}$				0.6	V	1
IL	Input current	DATA, E	NB	V <sub>I</sub> = 2.7 V				20	μΑ	
				V <sub>I</sub> = 0.4 V				-0.2	mA	•
		Сн		$V_I = 0$ to $V_{CC}$				±1	μΑ	•'
I <sub>SW</sub>	Switching	LD		CH = 3.0 V, Rs = 360 $\Omega$ , V <sub>L</sub>	<sub>D</sub> = 2 V		120		mA	2
	current (see note)		mperature efficient	Ta = 20 to 70°C			0.11		mA/°C	
I <sub>B</sub>	Bias current (see note)	LD		$VB = 1.2 \text{ V}, RB = 360 \Omega, V_L$	<sub>D</sub> = 2 V		30		mA	2
lcg	Load charging current	Сн		$\overline{\text{ENB}} = 0.8 \text{ V}, \text{ V}_{\text{O}} = 0.6 \text{ to } 4.0 \text{ M}_{\text{O}}$	0 V	-0.66		-2.0	mA	3
ldg	Load discharge current	Сн		$\overline{\text{ENB}} = 0.8 \text{ V}, \text{ V}_{\text{O}} = 0.6 \text{ to } 4.0 $	0 V	0.66		2.0	mA	3
loz	Output current in off state	Сн		$V_{O} = 0$ to $V_{CC}$ , Hold state				±5	μΑ	3
I <sub>OFF</sub>	Output current	LD		<u>ENB</u> = 0.8 V, <u>DATA</u> = 2.0 V	,		0.33	50	μΑ	2
	when off			<u>ENB</u> = 2.0 V, <u>DATA</u> = 0.8 V	1		0.01	50	_	
I <sub>CC</sub>	Power supply cur	rent		$V_{CC} = 5.25 \text{ V}, \overline{\text{ENB}} = 0 \text{ V},$ $C_H = 3.0 \text{ V}, V_B = 1.2 \text{ V},$	DATA = 0 V		54	75	mA	4
				$\begin{aligned} R_{\text{S}} &= 300~\Omega,~R_{\text{B}} = 360~\Omega,\\ R_{\text{O}} &= LD = 5.0~V \end{aligned}$	DATA = 4.5 V		52	74	_	

<sup>\*</sup>Typical values are for Ta = 25°C, V<sub>CC</sub> = 5 V.

Note: These quantities indicate the input voltage-output current conversion characteristic; I<sub>SW</sub> and I<sub>B</sub> should be used within the range of the rated values under recommended operating conditions.

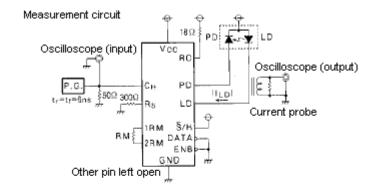
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# **Switching Characteristics**

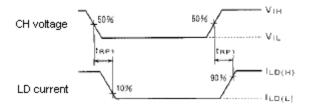
(	Ta	=	259	C.	V	$_{\rm CC} =$	5	V)	
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Symbol	Item	em Measurement pin Input Output		Measurement	Limits			Unit
				conditions	Min.	Тур.	Max.	•
f <sub>OP</sub>	Operating frequency					40		Mbps
t <sub>RP1</sub>	Circuit response time 1	C <sub>н</sub> voltage	LD current	$I_{LD(L)} = 0 \text{ mA}$ $I_{LD(H)} = 60 \text{ mA} \text{ (Note 1)}$			7	μs
				$I_{LD(L)} = 55 \text{ mA}$ $I_{LD(H)} = 65 \text{ mA} \text{ (Note 1)}$			2	μs
t <sub>RP2</sub>	Circuit response time 2	PD current	C <sub>H</sub> voltage	$I_{PD(L)} = 0 \text{ mA}$ $I_{PD(H)} = 2 \text{ mA}$ $RM = 1 \text{ k}\Omega$ (Note 2)			15	μs
				$ \Delta I_{PD}  = 0.2 \text{ mA}$ RM = 1 k $\Omega$ (Note 2)			8	μs
t <sub>RP3</sub>	Circuit response time 3	S/H voltage	C <sub>H</sub> voltage	$I_{PD} = 0$ mA, 2 mA RM = 1 k $\Omega$ , Vr = 1.2 V (Note 3)			1	μs
t <sub>ON</sub>	Circuit turn-on time	ENB voltage	LD current	$I_{LD(H)} = 60 \text{ mA} \text{ (Note 4)}$			5	μs
t <sub>OFF</sub>	Circuit turn-off time	ENB voltage	LD current	$I_{LD(H)} = 60 \text{ mA} \text{ (Note 4)}$			2	μs

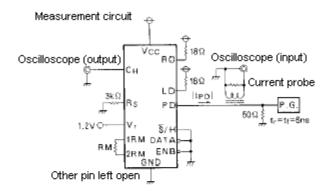
Note 1. Measurement circuit and Timing chart



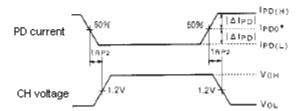
Timing chart



Note 2. Measurement circuit and Timing chart

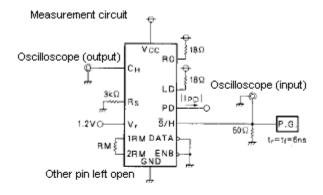


#### Timing chart

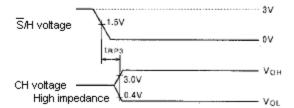


\*IPD when CH output is inverted

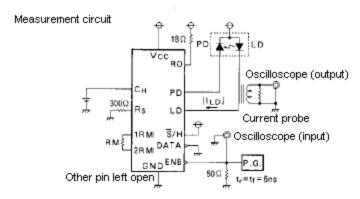
## Note 3. Measurement circuit and Timing chart

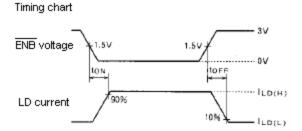


#### Timing chart

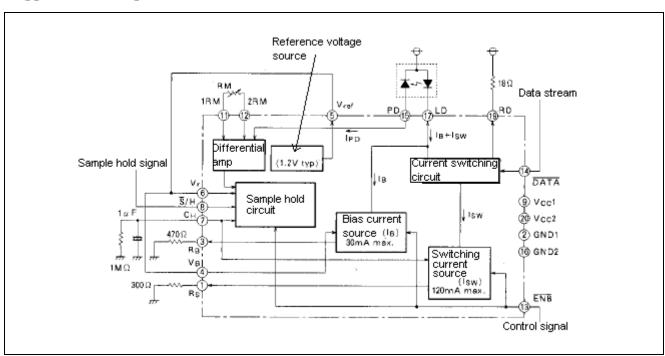


Note 4. Measurement circuit and Timing chart

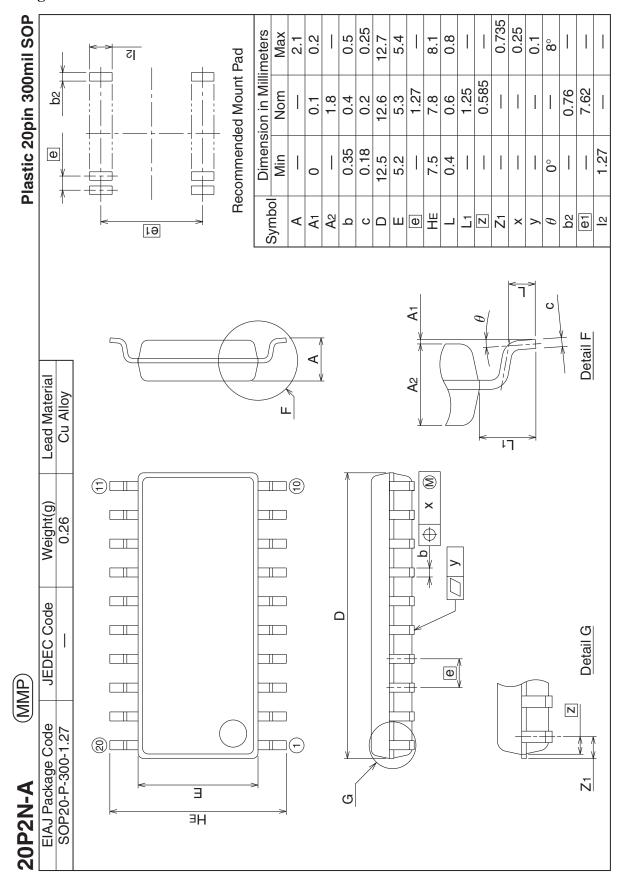




# **Application example**



# **Package Dimensions**



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